Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

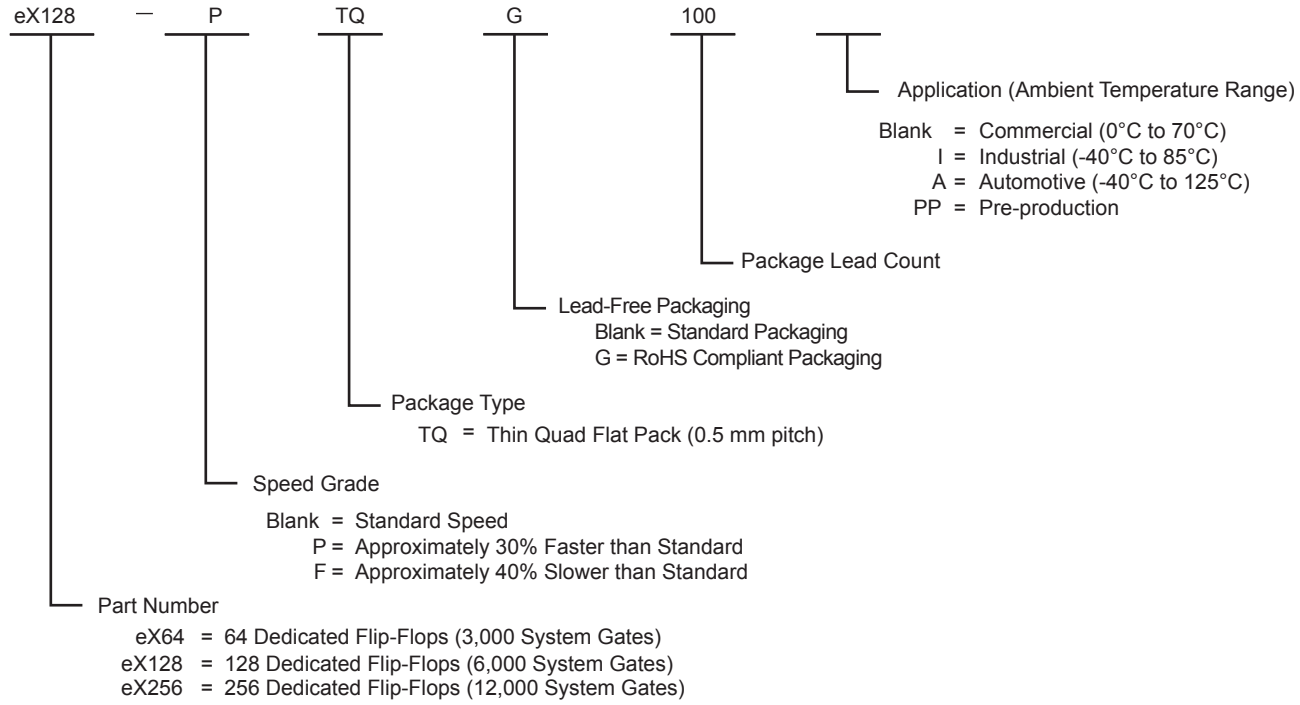
Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	256
Total RAM Bits	-
Number of I/O	46
Number of Gates	6000
Voltage - Supply	2.3V ~ 2.7V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	64-LQFP
Supplier Device Package	64-TQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/ex128-ptq64

Ordering Information



eX Device Status

eX Devices	Status
eX64	Production
eX128	Production
eX256	Production

Plastic Device Resources

Device	User I/Os (Including Clock Buffers)	
	TQ64	TQ100
eX64	41	56
eX128	46	70
eX256	—	81

Note: TQ = Thin Quad Flat Pack

1 – eX FPGA Architecture and Characteristics

General Description

The eX family of FPGAs is a low-cost solution for low-power, high-performance designs. The inherent low power attributes of the antifuse technology, coupled with an additional low static power mode, make these devices ideal for power-sensitive applications. Fabricated with an advanced 0.22 mm CMOS antifuse technology, these devices achieve high performance with no power penalty.

eX Family Architecture

Microsemi eX family is implemented on a high-voltage twin-well CMOS process using 0.22 µm design rules. The eX family architecture uses a “sea-of-modules” structure where the entire floor of the device is covered with a grid of logic modules with virtually no chip area lost to interconnect elements or routing. Interconnection among these logic modules is achieved using Microsemi patented metal-to-metal programmable antifuse interconnect elements. The antifuse interconnect is made up of a combination of amorphous silicon and dielectric material with barrier metals and has an "on" state resistance of 25Ω with a capacitance of 1.0fF for low-signal impedance. The antifuses are normally open circuit and, when programmed, form a permanent low-impedance connection. The eX family provides two types of logic modules, the register cell (R-cell) and the combinatorial cell (C-cell).

The R-cell contains a flip-flop featuring asynchronous clear, asynchronous preset, and clock enable (using the S0 and S1 lines) control signals (Figure 1-1). The R-cell registers feature programmable clock polarity selectable on a register-by-register basis. This provides additional flexibility while allowing mapping of synthesized functions into the eX FPGA. The clock source for the R-cell can be chosen from either the hard-wired clock or the routed clock.

The C-cell implements a range of combinatorial functions up to five inputs (Figure 1-2 on page 1-2). Inclusion of the DB input and its associated inverter function enables the implementation of more than 4,000 combinatorial functions in the eX architecture in a single module.

Two C-cells can be combined together to create a flip-flop to imitate an R-cell via the use of the CC macro. This is particularly useful when implementing non-timing-critical paths and when the design engineer is running out of R-cells. More information about the CC macro can be found in the *Maximizing Logic Utilization in eX, SX and SX-A FPGA Devices Using CC Macros* application note.

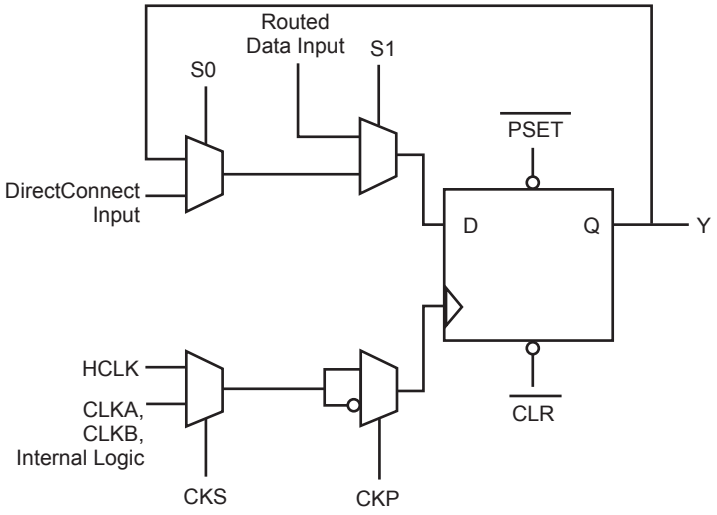


Figure 1-1 • **R-Cell**

Other Architectural Features

Performance

The combination of architectural features described above enables eX devices to operate with internal clock frequencies exceeding 350 MHz for very fast execution of complex logic functions. The eX family is an optimal platform upon which the functionality previously contained in CPLDs can be integrated. eX devices meet the performance goals of gate arrays, and at the same time, present significant improvements in cost and time to market. Using timing-driven place-and-route tools, designers can achieve highly deterministic device performance.

User Security

Microsemi FuseLock advantage provides the highest level of protection in the FPGA industry against unauthorized modifications. In addition to the inherent strengths of the architecture, special security fuses that are intended to prevent internal probing and overwriting are hidden throughout the fabric of the device. They are located such that they cannot be accessed or bypassed without destroying the rest of the device, making Microsemi antifuse FPGAs highly resistant to both invasive and more subtle noninvasive attacks.

Look for this symbol to ensure your valuable IP is secure. The FuseLock Symbol on the FPGA ensures that the device is safeguarded to cryptographic attacks.

Figure 1-7 • **Fuselock**

For more information, refer to *Implementation of Security in Microsemi Antifuse FPGAs* application note.

I/O Modules

Each I/O on an eX device can be configured as an input, an output, a tristate output, or a bidirectional pin. Even without the inclusion of dedicated I/O registers, these I/Os, in combination with array registers, can achieve clock-to-out (pad-to-pad) timing as fast as 3.9 ns. I/O cells in eX devices do not contain embedded latches or flip-flops and can be inferred directly from HDL code. The device can easily interface with any other device in the system, which in turn enables parallel design of system components and reduces overall design time.

All unused I/Os are configured as tristate outputs by Microsemi's Designer software, for maximum flexibility when designing new boards or migrating existing designs. Each I/O module has an available pull-up or pull-down resistor of approximately 50 kΩ that can configure the I/O in a known state during power-up. Just shortly before V_{CCA} reaches 2.5 V, the resistors are disabled and the I/Os will be controlled by user logic.

Table 1-2 describes the I/O features of eX devices. For more information on I/Os, refer to *Microsemi eX, SX-A, and RT54SX-S I/Os* application note.

Table 1-2 • **I/O Features**

Function	Description
Input Buffer Threshold Selection	• 5.0V TTL • 3.3V LVTTL • 2.5V LVCMOS2
Nominal Output Drive	• 5.0V TTL/CMOS • 3.3V LVTTL • 2.5V LVCMOS 2
Output Buffer	"Hot-Swap" Capability • I/O on an unpowered device does not sink current • Can be used for "cold sparing" Selectable on an individual I/O basis Individually selectable low-slew option
Power-Up	Individually selectable pull ups and pull downs during power-up (default is to power up in tristate) Enables deterministic power-up of device V_{CCA} and V_{CCI} can be powered in any order

The eX family supports mixed-voltage operation and is designed to tolerate 5.0 V inputs in each case.

A detailed description of the I/O pins in eX devices can be found in "Pin Description" on page 1-31.

Hot-Swapping

eX I/Os are configured to be hot-swappable. During power-up/down (or partial up/down), all I/Os are tristated, provided V_{CCA} ramps up within a diode drop of V_{CCI}. V_{CCA} and V_{CCI} do not have to be stable. during power-up/down, and they do not require a specific power-up or power-down sequence in order to avoid damage to the eX devices. In addition, all outputs can be programmed to have a weak resistor pull-up or pull-down for output tristate at power-up. After the eX device is plugged into an electrically active system, the device will not degrade the reliability of or cause damage to the host system. The device's output pins are driven to a high impedance state until normal chip operating conditions are reached. Please see the application note, *Microsemi SX-A and RT54SX-S Devices in Hot-Swap and Cold-Sparing Applications*, which also applies to the eX devices, for more information on hot swapping.

Power Requirements

Power consumption is extremely low for the eX family due to the low capacitance of the antifuse interconnects. The antifuse architecture does not require active circuitry to hold a charge (as do SRAM or EPROM), making it the lowest-power FPGA architecture available today.

Low Power Mode

The eX family has been designed with a Low Power Mode. This feature, activated with setting the special LP pin to HIGH for a period longer than 800 ns, is particularly useful for battery-operated systems where battery life is a primary concern. In this mode, the core of the device is turned off and the device consumes minimal power with low standby current. In addition, all input buffers are turned off, and all outputs and bidirectional buffers are tristated when the device enters this mode. Since the core of the device is turned off, the states of the registers are lost. The device must be re-initialized when returning to normal operating mode. I/Os can be driven during LP mode. For details, refer to the *Design for Low Power in Microsemi Antifuse FPGAs* application note under the section Using the LP Mode Pin on eX Devices. Clock pins should be driven either HIGH or LOW and should not float; otherwise, they will draw current and burn power. The device must be re-initialized when exiting LP mode.

To exit the LP mode, the LP pin must be driven LOW for over 200 µs to allow for the charge pumps to power-up and device initialization can begin.

Table 1-3 illustrates the standby current of eX devices in LP mode.

Table 1-3 • **Standby Power of eX Devices in LP Mode Typical Conditions, V_{CCA}, V_{CCI} = 2.5 V, T_J = 25° C**

Product	Low Power Standby Current	Units
eX64	100	µA
eX128	111	µA
eX256	134	µA

Designer software is a place-and-route tool and provides a comprehensive suite of backend support tools for FPGA development. The Designer software includes timing-driven place-and-route, and a world-class integrated static timing analyzer and constraints editor. With the Designer software, a user can lock his/her design pins before layout while minimally impacting the results of place-and-route. Additionally, the back-annotation flow is compatible with all the major simulators and the simulation results can be cross-probed with Silicon Explorer II, Microsemi integrated verification and logic analysis tool. Another tool included in the Designer software is the SmartGen core generator, which easily creates popular and commonly used logic functions for implementation into your schematic or HDL design. Microsemi's Designer software is compatible with the most popular FPGA design entry and verification tools from companies such as Mentor Graphics, Synplicity, Synopsys, and Cadence Design Systems. The Designer software is available for both the Windows and UNIX operating systems.

Related Documents

Datasheet

eX Automotive Family FPGAs
www.microsemi.com/soc/documents/eX_Auto_DS.pdf

Application Notes

Maximizing Logic Utilization in eX, SX and SX-A FPGA Devices Using CC Macros
www.microsemi.com/soc/documents/CC_Macro_AN.pdf
Implementation of Security in Microsemi Antifuse FPGAs
www.microsemi.com/soc/documents/Antifuse_Security_AN.pdf
Microsemi eX, SX-A, and RT54SX-S I/Os
www.microsemi.com/soc/documents/antifuseIO_AN.pdf
Microsemi SX-A and RT54SX-S Devices in Hot-Swap and Cold-Sparing Applications
www.microsemi.com/soc/documents/HotSwapColdSparing_AN.pdf
Design For Low Power in Microsemi Antifuse FPGAs
www.microsemi.com/soc/documents/Low_Power_AN.pdf
Programming Antifuse Devices
www.microsemi.com/soc/documents/AntifuseProgram_AN.pdf

User Guides

Silicon Sculptor II User's Guide
www.microsemi.com/soc/documents/SiliSculptII_Sculpt3_ug.pdf

Miscellaneous

Libero IDE flow
www.microsemi.com/soc/products/tools/libero/flow.html

2.5 V / 3.3 V /5.0 V Operating Conditions

Table 1-9 • **Absolute Maximum Ratings***

Symbol	Parameter	Limits	Units
VCCI	DC Supply Voltage for I/Os	–0.3 to +6.0	V
VCCA	DC Supply Voltage for Array	–0.3 to +3.0	V
VI	Input Voltage	–0.5 to +5.75	V
VO	Output Voltage	–0.5 to +V_{CCI}	V
T_{STG}	Storage Temperature	–65 to +150	°C

*Note: *Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. Exposure to absolute maximum rated conditions for extended periods may affect device reliability. Devices should not be operated outside the Recommended Operating Conditions.*

Table 1-10 • **Recommended Operating Conditions**

Parameter	Commercial	Industrial	Units
Temperature Range*	0 to +70	–40 to +85	°C
2.5V Power Supply Range (VCCA, VCCI)	2.3 to 2.7	2.3 to 2.7	V
3.3V Power Supply Range (VCCI)	3.0 to 3.6	3.0 to 3.6	V
5.0V Power Supply Range (VCCI)	4.75 to 5.25	4.75 to 5.25	V

*Note: *Ambient temperature (T_A).*

Table 1-11 • **Typical eX Standby Current at 25°C**

Product	VCCA= 2.5 V VCCI = 2.5 V	VCCA = 2.5 V VCCI = 3.3 V	VCCA = 2.5 V VCCI = 5.0 V
eX64	397 µA	497 µA	700 µA
eX128	696 µA	795 µA	1,000 µA
eX256	698 µA	796 µA	2,000 µA

Power Dissipation

Power consumption for eX devices can be divided into two components: static and dynamic.

Static Power Component

The power due to standby current is typically a small component of the overall power. Typical standby current for eX devices is listed in the Table 1-11 on page 1-16. For example, the typical static power for eX128 at 3.3 V V_{CCI} is:

ICC * VCCA = 795 µA x 2.5 V = 1.99 mW

Dynamic Power Component

Power dissipation in CMOS devices is usually dominated by the dynamic power dissipation. This component is frequency-dependent and a function of the logic and the external I/O. Dynamic power dissipation results from charging internal chip capacitance due to PC board traces and load device inputs. An additional component of the dynamic power dissipation is the totem pole current in the CMOS transistor pairs. The net effect can be associated with an equivalent capacitance that can be combined with frequency and voltage to represent dynamic power dissipation.

Dynamic power dissipation = CEQ * $VCCA^2$ x F

where:

CEQ = Equivalent capacitance

F = switching frequency

Equivalent capacitance is calculated by measuring ICCA at a specified frequency and voltage for each circuit component of interest. Measurements have been made over a range of frequencies at a fixed value of VCC. Equivalent capacitance is frequency-independent, so the results can be used over a wide range of operating conditions. Equivalent capacitance values are shown below.

CEQ Values for eX Devices

Combinatorial modules (Ceqcm)	1.70 pF
Sequential modules (Ceqsm)	1.70 pF
Input buffers (Ceqi)	1.30 pF
Output buffers (Ceqo)	7.40 pF
Routed array clocks (Ceqcr)	1.05 pF

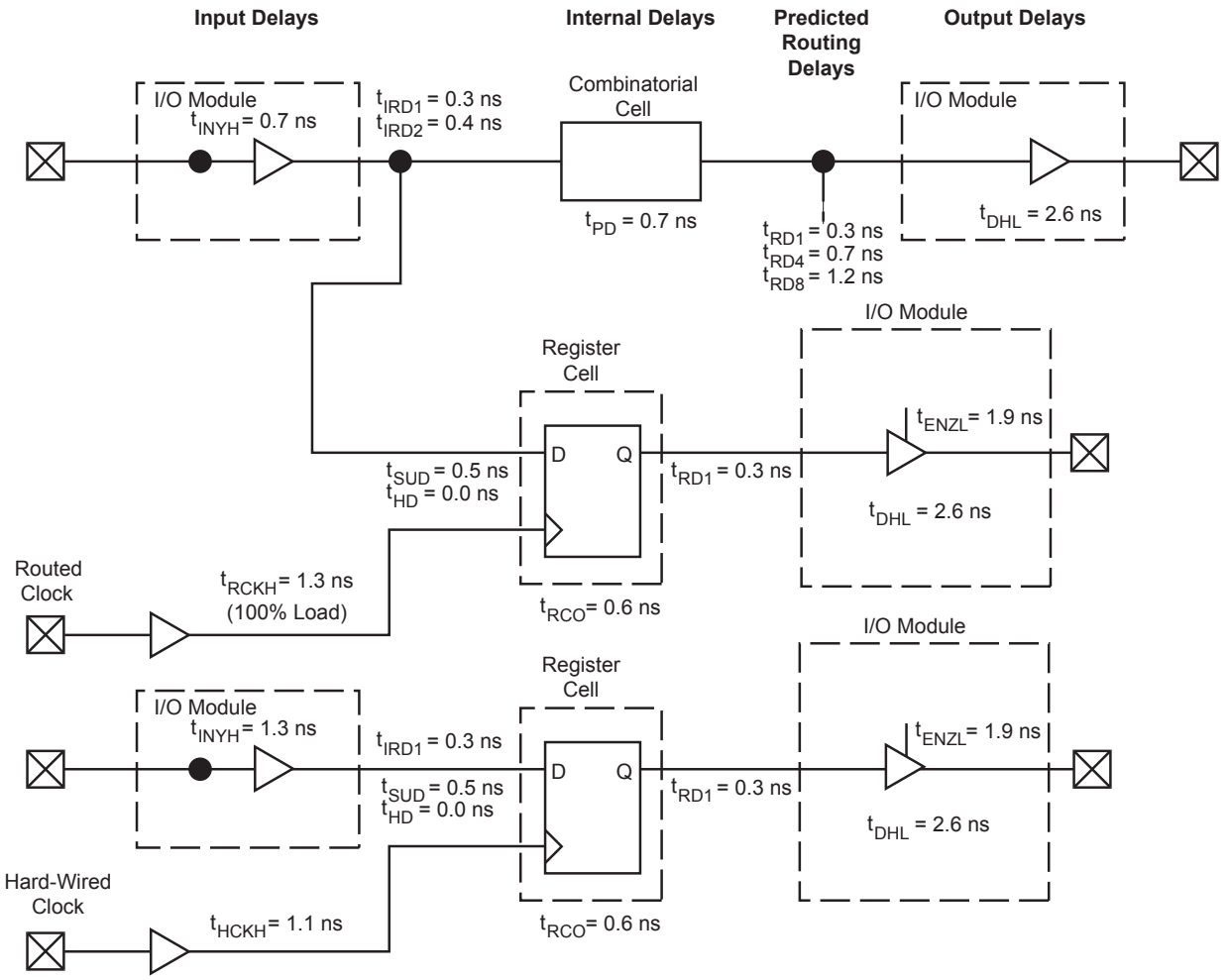
The variable and fixed capacitance of other device components must also be taken into account when estimating the dynamic power dissipation.

Table 1-12 shows the capacitance of the clock components of eX devices.

***Table 1-12* • Capacitance of Clock Components of eX Devices**

	eX64	eX128	eX256
Dedicated array clock – variable (Ceqhv)	0.85 pF	0.85 pF	0.85 pF
Dedicated array clock – fixed (Ceqhf)	18.00 pF	20.00 pF	25.00 pF
Routed array clock A (r1)	23.00 pF	28.00 pF	35.00 pF
Routed array clock B (r2)	23.00 pF	28.00 pF	35.00 pF

eX Timing Model



Note: Values shown for eX128–P, worst-case commercial conditions (5.0 V, 35 pF Pad Load).

Figure 1-14 • **eX Timing Model**

Hardwired Clock

External Setup = $t_{INYH} + t_{IRD1} + t_{SUD} – t_{HCKH}$

= 0.7 + 0.3 + 0.5 – 1.1 = 0.4 ns

Clock-to-Out (Pad-to-Pad), typical

= $t_{HCKH} + t_{RCO} + t_{RD1} + t_{DHL}$

= 1.1 + 0.6 + 0.3 + 2.6 = 4.6 ns

Routed Clock

External Setup = $t_{INYH} + t_{IRD2} + t_{SUD} – t_{RCKH}$

= 0.7 + 0.4 + 0.5 – 1.3= 0.3 ns

Clock-to-Out (Pad-to-Pad), typical

= $t_{RCKH} + t_{RCO} + t_{RD1} + t_{DHL}$

= 1.3+ 0.6 + 0.3 + 2.6 = 4.8 ns

Output Buffer Delays

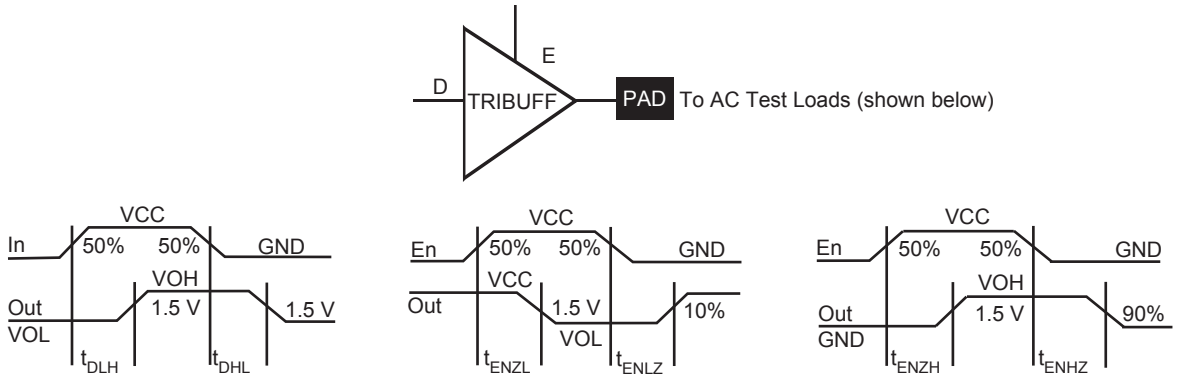


***Table 1-13* • Output Buffer Delays**

AC Test Loads

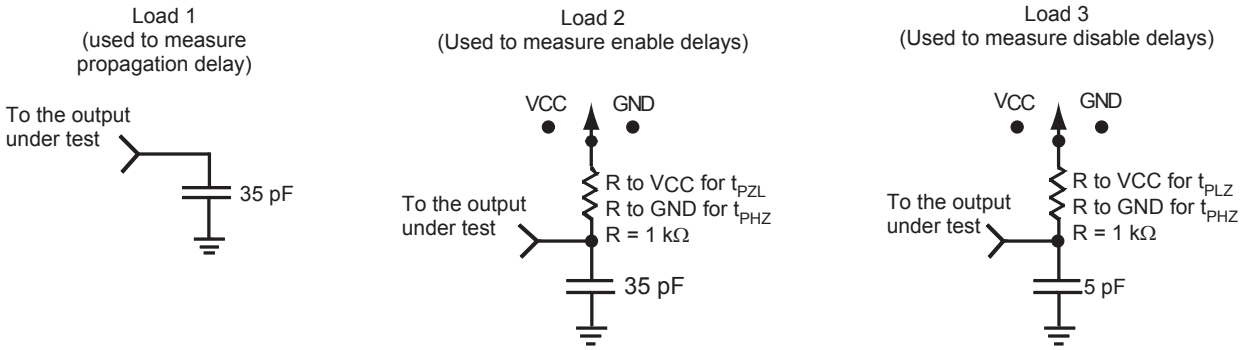


***Figure 1-15* • AC Test Loads**

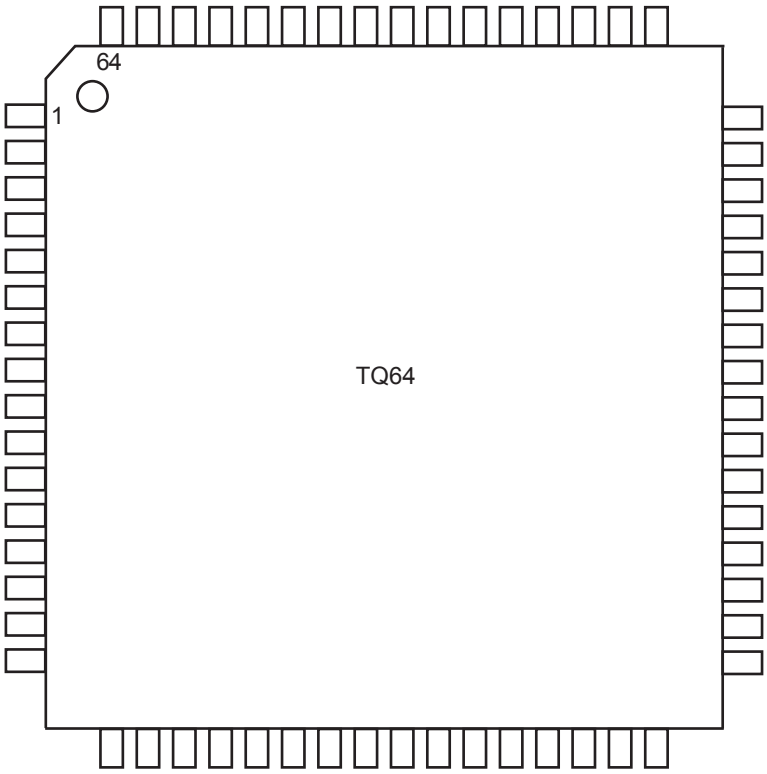
Table 1-20 • **eX Family Timing Characteristics**
(Worst-Case Commercial Conditions VCCA = 2.3 V, T_J = 70°C)

		–P Speed		Std Speed		–F Speed		
Parameter	**Description**	**Min.**	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	**Units**
2.5 V LVCMOS Output Module Timing[1] (VCCI = 2.3 V)								
t_{DLH}	Data-to-Pad LOW to HIGH		3.3		4.7		6.6	ns
t_{DHL}	Data-to-Pad HIGH to LOW		3.5		5.0		7.0	ns
t_{DHLS}	Data-to-Pad HIGH to LOW—Low Slew		11.6		16.6		23.2	ns
t_{ENZL}	Enable-to-Pad, Z to L		2.5		3.6		5.1	ns
t_{ENZLS}	Enable-to-Pad Z to L—Low Slew		11.8		16.9		23.7	ns
t_{ENZH}	Enable-to-Pad, Z to H		3.4		4.9		6.9	ns
t_{ENLZ}	Enable-to-Pad, L to Z		2.1		3.0		4.2	ns
t_{ENHZ}	Enable-to-Pad, H to Z		2.4		5.67		7.94	ns
d_{TLH}	Delta Delay vs. Load LOW to HIGH		0.034		0.046		0.066	ns/pF
d_{THL}	Delta Delay vs. Load HIGH to LOW		0.016		0.022		0.05	ns/pF
d_{THLS}	Delta Delay vs. Load HIGH to LOW—Low Slew		0.05		0.072		0.1	ns/pF
3.3 V LVTTL Output Module Timing[1] (VCCI = 3.0 V)								
t_{DLH}	Data-to-Pad LOW to HIGH		2.8		4.0		5.6	ns
t_{DHL}	Data-to-Pad HIGH to LOW		2.7		3.9		5.4	ns
t_{DHLS}	Data-to-Pad HIGH to LOW—Low Slew		9.7		13.9		19.5	ns
t_{ENZL}	Enable-to-Pad, Z to L		2.2		3.2		4.4	ns
t_{ENZLS}	Enable-to-Pad Z to L—Low Slew		9.7		13.9		19.6	ns
t_{ENZH}	Enable-to-Pad, Z to H		2.8		4.0		5.6	ns
t_{ENLZ}	Enable-to-Pad, L to Z		2.8		4.0		5.6	ns
t_{ENHZ}	Enable-to-Pad, H to Z		2.6		3.8		5.3	ns
d_{TLH}	Delta Delay vs. Load LOW to HIGH		0.02		0.03		0.046	ns/pF
d_{THL}	Delta Delay vs. Load HIGH to LOW		0.016		0.022		0.05	ns/pF
d_{THLS}	Delta Delay vs. Load HIGH to LOW—Low Slew		0.05		0.072		0.1	ns/pF
5.0 V TTL Output Module Timing* (VCCI = 4.75 V)								
t_{DLH}	Data-to-Pad LOW to HIGH		2.0		2.9		4.0	ns
t_{DHL}	Data-to-Pad HIGH to LOW		2.6		3.7		5.2	ns
t_{DHLS}	Data-to-Pad HIGH to LOW—Low Slew		6.8		9.7		13.6	ns
t_{ENZL}	Enable-to-Pad, Z to L		1.9		2.7		3.8	ns
t_{ENZLS}	Enable-to-Pad Z to L—Low Slew		6.8		9.8		13.7	ns
t_{ENZH}	Enable-to-Pad, Z to H		2.1		3.0		4.1	ns
t_{ENLZ}	Enable-to-Pad, L to Z		3.3		4.8		6.6	ns

*Note: *Delays based on 35 pF loading.*

2 – Package Pin Assignments

TQ64



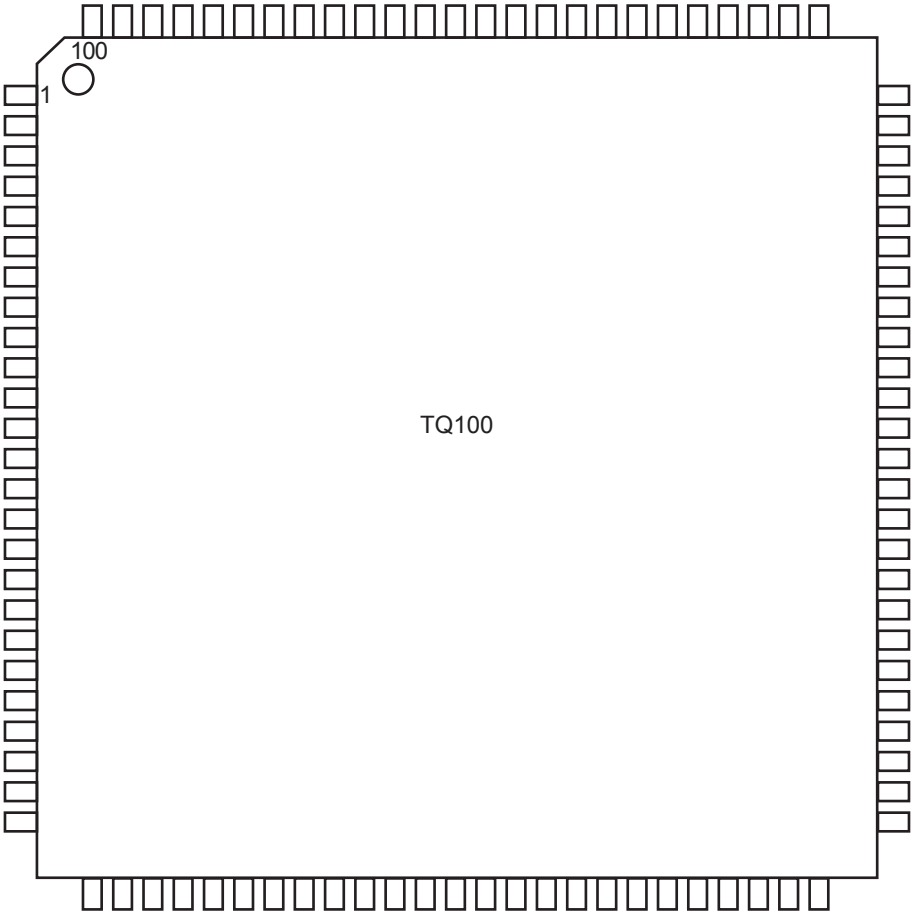
Note: For Package Manufacturing and Environmental information, visit Resource center at www.microsemi.com/soc/products/rescenter/package/index.html.

TQ64		
Pin Number	eX64 Function	eX128 Function
1	GND	GND
2	TDI, I/O	TDI, I/O
3	I/O	I/O
4	TMS	TMS
5	GND	GND
6	VCCI	VCCI
7	I/O	I/O
8	I/O	I/O
9	NC	I/O
10	NC	I/O
11	TRST, I/O	TRST, I/O
12	I/O	I/O
13	NC	I/O
14	GND	GND
15	I/O	I/O
16	I/O	I/O
17	I/O	I/O
18	I/O	I/O
19	VCCI	VCCI
20	I/O	I/O
21	PRB, I/O	PRB, I/O
22	VCCA	VCCA
23	GND	GND
24	I/O	I/O
25	HCLK	HCLK
26	I/O	I/O
27	I/O	I/O
28	I/O	I/O
29	I/O	I/O
30	I/O	I/O
31	I/O	I/O
32	TDO, I/O	TDO, I/O

TQ64		
Pin Number	eX64 Function	eX128 Function
33	GND	GND
34	I/O	I/O
35	I/O	I/O
36	VCCA	VCCA
37	VCCI	VCCI
38	I/O	I/O
39	I/O	I/O
40	NC	I/O
41	NC	I/O
42	I/O	I/O
43	I/O	I/O
44	VCCA	VCCA
45*	GND/LP	GND/ LP
46	GND	GND
47	I/O	I/O
48	I/O	I/O
49	I/O	I/O
50	I/O	I/O
51	I/O	I/O
52	VCCI	VCCI
53	I/O	I/O
54	I/O	I/O
55	CLKA	CLKA
56	CLKB	CLKB
57	VCCA	VCCA
58	GND	GND
59	PRA, I/O	PRA, I/O
60	I/O	I/O
61	VCCI	VCCI
62	I/O	I/O
63	I/O	I/O
64	TCK, I/O	TCK, I/O

*Note: *Please read the LP pin descriptions for restrictions on their use.*

TQ100



Note: For Package Manufacturing and Environmental information, visit Resource center at www.microsemi.com/soc/products/rescenter/package/index.html.

TQ100			
Pin Number	eX64 Function	eX128 Function	eX256 Function
1	GND	GND	GND
2	TDI, I/O	TDI, I/O	TDI, I/O
3	NC	NC	I/O
4	NC	NC	I/O
5	NC	NC	I/O
6	I/O	I/O	I/O
7	TMS	TMS	TMS
8	VCCI	VCCI	VCCI
9	GND	GND	GND
10	NC	I/O	I/O
11	NC	I/O	I/O
12	I/O	I/O	I/O
13	NC	I/O	I/O
14	I/O	I/O	I/O
15	NC	I/O	I/O
16	TRST, I/O	TRST, I/O	TRST, I/O
17	NC	I/O	I/O
18	I/O	I/O	I/O
19	NC	I/O	I/O
20	VCCI	VCCI	VCCI
21	I/O	I/O	I/O
22	NC	I/O	I/O
23	NC	NC	I/O
24	NC	NC	I/O
25	I/O	I/O	I/O
26	I/O	I/O	I/O
27	I/O	I/O	I/O
28	I/O	I/O	I/O
29	I/O	I/O	I/O
30	I/O	I/O	I/O
31	I/O	I/O	I/O
32	I/O	I/O	I/O
33	I/O	I/O	I/O
34	PRB, I/O	PRB, I/O	PRB, I/O
35	VCCA	VCCA	VCCA

TQ100			
Pin Number	eX64 Function	eX128 Function	eX256 Function
36	GND	GND	GND
37	NC	NC	NC
38	I/O	I/O	I/O
39	HCLK	HCLK	HCLK
40	I/O	I/O	I/O
41	I/O	I/O	I/O
42	I/O	I/O	I/O
43	I/O	I/O	I/O
44	VCCI	VCCI	VCCI
45	I/O	I/O	I/O
46	I/O	I/O	I/O
47	I/O	I/O	I/O
48	I/O	I/O	I/O
49	TDO, I/O	TDO, I/O	TDO, I/O
50	NC	I/O	I/O
51	GND	GND	GND
52	NC	NC	I/O
53	NC	NC	I/O
54	NC	NC	I/O
55	I/O	I/O	I/O
56	I/O	I/O	I/O
57	VCCA	VCCA	VCCA
58	VCCI	VCCI	VCCI
59	NC	I/O	I/O
60	I/O	I/O	I/O
61	NC	I/O	I/O
62	I/O	I/O	I/O
63	NC	I/O	I/O
64	I/O	I/O	I/O
65	NC	I/O	I/O
66	I/O	I/O	I/O
67	VCCA	VCCA	VCCA
68	GND/LP	GND/LP	GND/LP
69	GND	GND	GND
70	I/O	I/O	I/O

*Note: *Please read the LP pin descriptions for restrictions on their use.*

3 – Datasheet Information

List of Changes

The following table lists critical changes that were made in the current version of the document.

Revision	Changes	Page
Revision 10 (October 2012)	The "User Security" section was revised to clarify that although no existing security measures can give an absolute guarantee, Microsemi FPGAs implement industry standard security (SAR 34677).	1-5
	Package names used in the "Product Profile" section and "Package Pin Assignments" section were revised to match standards given in *Package Mechanical Drawings* (SAR 34779).	I 2-1
Revision 9 (June 2011)	The versioning system for datasheets has been changed. Datasheets are assigned a revision number that increments each time the datasheet is revised. The "eX Device Status" table indicates the status for each device in the device family.	II
	The Chip Scale packages (CS49, CS128, CS181) are no longer offered for eX devices. They have been removed from the product family information. Pin tables for CSP packages have been removed from the datasheet (SAR 32002).	N/A
Revision 8 (v4.3, June 2006)	The "Ordering Information" was updated with RoHS information. The TQFP measurement was also updated.	II
	The "Dedicated Test Mode" was updated.	1-10
	Note 5 was added to the "3.3 V LVTTL Electrical Specifications" and "5.0 V TTL Electrical Specifications" tables	1-18
	The "LP Low Power Pin" description was updated.	1-31
Revision 7 (v4.2, June 2004)	The "eX Timing Model" was updated.	1-22
v4.1	The "Development Tool Support" section was updated.	1-13
	The "Package Thermal Characteristics" section was updated.	1-21
v4.0	The "Product Profile" section was updated.	1-I
	The "Ordering Information" section was updated.	1-II
	The "Temperature Grade Offerings" section is new.	1-III
	The "Speed Grade and Temperature Grade Matrix" section is new.	1-III
	The "eX FPGA Architecture and Characteristics" section was updated.	1-1
	The "Clock Resources" section was updated.	1-3
	Table 1-1 •Connections of Routed Clock Networks, CLKA and CLKB is new.	1-4
	The "User Security" section was updated.	1-5
	The "I/O Modules" section was updated.	1-5
	The "Hot-Swapping" section was updated.	1-6
	The "Power Requirements" section was updated.	1-6
	The "Low Power Mode" section was updated.	1-6
	The "Boundary Scan Testing (BST)" section was updated.	1-10
	The "Dedicated Test Mode" section was updated.	1-10

Revision	Changes	Page
Advance v0.4	In the Product Profile, the Maximum User I/Os for eX64 was changed to 84.	1-I
	In the Product Profile table, the Maximum User I/Os for eX128 was changed to 100.	1-I
Advance v0.3	The Mechanical Drawings section has been removed from the data sheet. The mechanical drawings are now contained in a separate document, “Package Characteristics and Mechanical Drawings,” available on the Actel web site.	
	A new section describing "Clock Resources"has been added.	1-3
	A new table describing "I/O Features"has been added.	1-6
	The "Pin Description"section has been updated and clarified.	1-31
	The original Electrical Specifications table was separated into two tables (2.5V and 3.3/5.0V). In both tables, several different currents are specified for V_{OH} and V_{OL}.	Page 8 and 9
	A new table listing 2.5V low power specifications and associated power graphs were added.	page 9
	Pin functions for eX256 TQ100 have been added to the "TQ100"table.	2-3
	A CS49 pin drawing and pin assignment table including eX64 and eX128 pin functions have been added.	page 26
	A CS128 pin drawing and pin assignment table including eX64, eX128, and eX256 pin functions have been added.	pages 26-27
	A CS180 pin drawing and pin assignment table for eX256 pin functions have been added.	pages 27, 31
Advance v0.2	The following table note was added to the eX Timing Characteristics table for clarification: Clock skew improves as the clock network becomes more heavily loaded.	pages 14-15

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